

## SILICON BRIDGE RECTIFIERS

## SBD114

### FEATURES

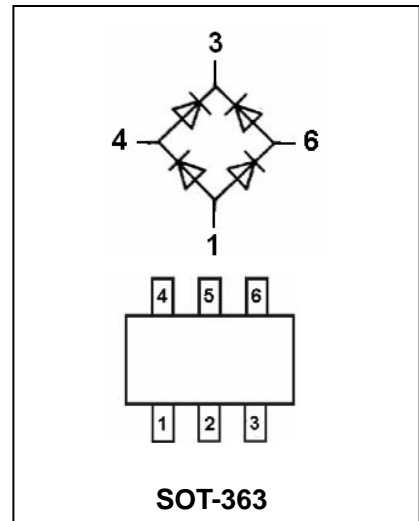
- Low Forward Voltage Drop.
- Guard Ring Construction For Transient Protection.
- Negligible Reverse Recovery Time.
- Low Reverse Capacitance.



Lead-free

### APPLICATIONS

- Schottky barrier switching.



### ORDERING INFORMATION

Type No.	Marking	Package Code
SBD114	S114	SOT-363

### MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Peak Repetitive Peak reverse voltage Working Peak DC Reverse Voltage	$V_{RR}$ $V_{RWM}$ $V_R$	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Forward Continuous Current	$I_F$	350	mA
Repetitive Peak Forward Current @t≤1.0s	$I_{FRM}$	1.5	A
Power Dissipation	$P_d$	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	300	°C/W
Storage temperature	$T_{stg}$	-65 to +125	°C



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**ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	40			V	$I_R=10\mu A$
Forward voltage	$V_F$			0.37 0.60	V	$I_F=20mA$ $I_F=200mA$
Reverse current	$I_{RM}$			5.0	$\mu A$	$V_R=30V$
Capacitance between terminals	$C_T$		50		pF	$V_R=0, f=1MHz$
Reverse Recovery Time	$t_{rr}$		10		ns	$I_R=I_F=200mA$ $I_{rr}=0.1*I_R, R_L=100\Omega$

**TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

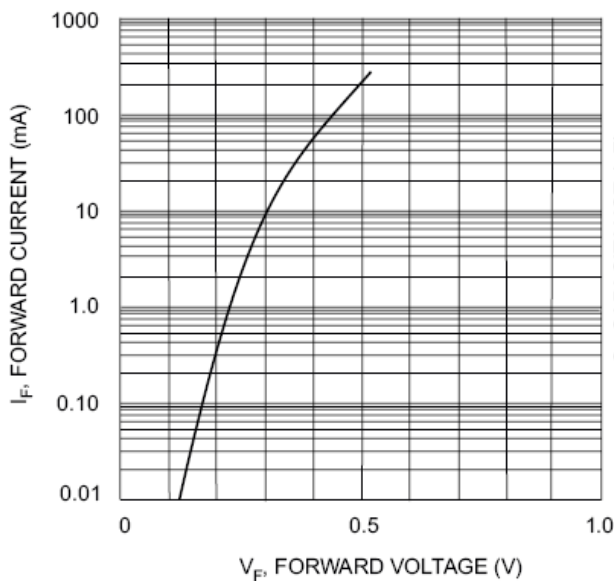


Fig. 1 Typical Forward Characteristics

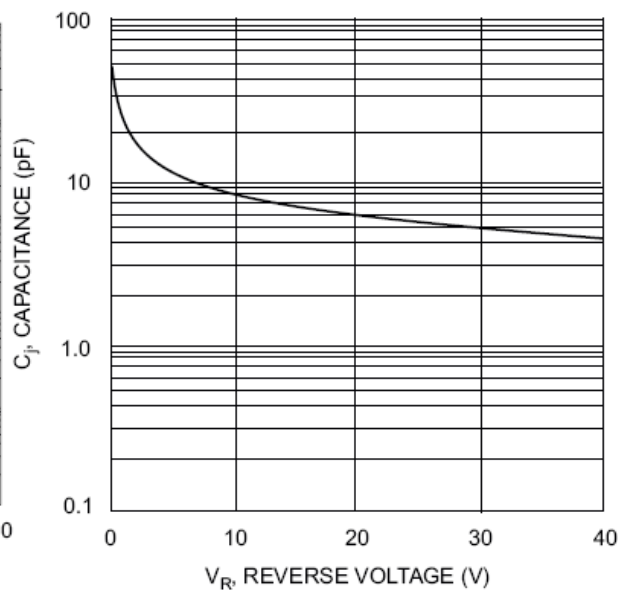


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage

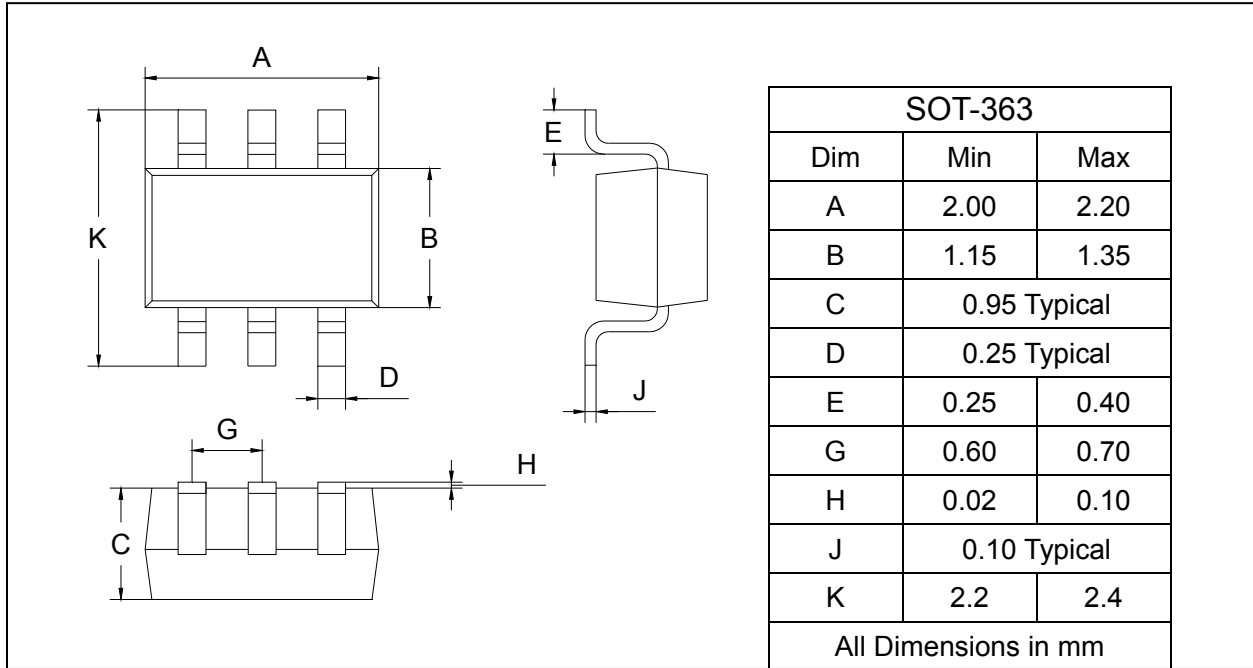
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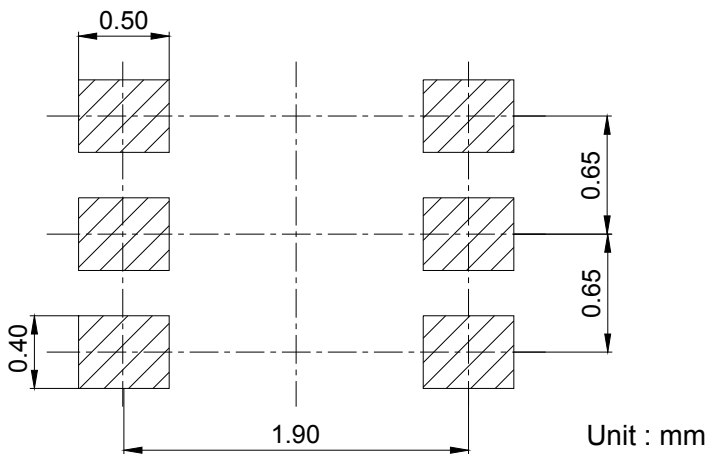
## PACKAGE OUTLINE

Plastic surface mounted package

SOT-363



## SOLDERING FOOTPRINT



## PACKAGE INFORMATION

Device	Package	Shipping
SBD114	SOT-363	3000/Tape&Reel